



### **UNR411H00A Information**



For Reference Only

Part Number UNR411H00A

Manufacturer Panasonic Electronic Components
Category Discrete Semiconductor Products

Transistors - Bipolar (BJT) - Single, Pre-Biased

**Description** TRANS PREBIAS PNP 300MW NS-B1

Package NS-B

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **UNR411H00A Specifications**

Manufacturer Part NumberUNR411H00AManufacturerPanasonic Electronic ComponentsCategoryDiscrete Semiconductor ProductsTransistors - Bipolar (BJT) - Single, Pre-BiasedPackageNS-B1Series-Transistor TypePNP - Pre-BiasedCurrent - Collector (Ic) (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)2.2kResistor - Emitter Base (R2) (Ohms)10kDC Current Gain (hFE) (Min) @ Ic, Vce30 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 300μA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition80MHzPower - Max300mWMounting TypeThrough HolePackage / CaseNS-B1Supplier Device PackageNS-B1	•	
Category  Discrete Semiconductor Products  Transistors - Bipolar (BJT) - Single, Pre-Biased  NS-B1  Series  - Transistor Type  PNP - Pre-Biased  Current - Collector (Ic) (Max)  Voltage - Collector Emitter Breakdown (Max)  Resistor - Base (R1) (Ohms)  Resistor - Emitter Base (R2) (Ohms)  DC Current Gain (hFE) (Min) @ Ic, Vce  30 @ 5mA, 10V  Vce Saturation (Max) @ Ib, Ic  250mV @ 300µA, 10mA  Current - Collector Cutoff (Max)  Frequency - Transition  80MHz  Power - Max  Mounting Type  Through Hole  Package / Case  NS-B1  Supplier Device Package	Manufacturer Part Number	UNR411H00A
Transistors - Bipolar (BJT) - Single, Pre-Biased  NS-B1  Series - Transistor Type PNP - Pre-Biased Current - Collector (Ic) (Max) Voltage - Collector Emitter Breakdown (Max)  Resistor - Base (R1) (Ohms) 2.2k  Resistor - Emitter Base (R2) (Ohms) 10k  DC Current Gain (hFE) (Min) @ Ic, Vce 30 @ 5mA, 10V  Vce Saturation (Max) @ Ib, Ic 250mV @ 300μA, 10mA  Current - Collector Cutoff (Max) Frequency - Transition 80MHz Power - Max Mounting Type Through Hole Package / Case NS-B1  Supplier Device Package	Manufacturer	Panasonic Electronic Components
PackageNS-B1Series-Transistor TypePNP - Pre-BiasedCurrent - Collector (Ic) (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)2.2kResistor - Emitter Base (R2) (Ohms)10kDC Current Gain (hFE) (Min) @ Ic, Vce30 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 300μA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition80MHzPower - Max300mWMounting TypeThrough HolePackage / CaseNS-B1Supplier Device PackageNS-B1	Category	Discrete Semiconductor Products
Series - Transistor Type PNP - Pre-Biased Current - Collector (Ic) (Max) 100mA Voltage - Collector Emitter Breakdown (Max) 50V Resistor - Base (R1) (Ohms) 2.2k Resistor - Emitter Base (R2) (Ohms) 10k DC Current Gain (hFE) (Min) @ Ic, Vce 30 @ 5mA, 10V Vce Saturation (Max) @ Ib, Ic 250mV @ 300µA, 10mA Current - Collector Cutoff (Max) 500nA Frequency - Transition 80MHz Power - Max 300mW Mounting Type Through Hole Package / Case NS-B1 Supplier Device Package		Transistors - Bipolar (BJT) - Single, Pre-Biased
Transistor Type  Current - Collector (Ic) (Max)  Voltage - Collector Emitter Breakdown (Max)  Resistor - Base (R1) (Ohms)  Resistor - Emitter Base (R2) (Ohms)  DC Current Gain (hFE) (Min) @ Ic, Vce  Vce Saturation (Max) @ Ib, Ic  Current - Collector Cutoff (Max)  Frequency - Transition  Power - Max  Mounting Type  Through Hole  Package / Case  Supplier Device Package  PNP - Pre-Biased  100mA  100mA  50V  2.2k  30 @ 5mA, 10V  250mV @ 300μA, 10mA  500nA  500nA  Through Hole  NS-B1	Package	NS-B1
Current - Collector (Ic) (Max)  Voltage - Collector Emitter Breakdown (Max)  Resistor - Base (R1) (Ohms)  Resistor - Emitter Base (R2) (Ohms)  DC Current Gain (hFE) (Min) @ Ic, Vce  30 @ 5mA, 10V  Vce Saturation (Max) @ Ib, Ic  Current - Collector Cutoff (Max)  Frequency - Transition  80MHz  Power - Max  300mW  Mounting Type  Through Hole  Package / Case  NS-B1  Supplier Device Package	Series	-
Voltage - Collector Emitter Breakdown (Max)  Resistor - Base (R1) (Ohms)  2.2k  Resistor - Emitter Base (R2) (Ohms)  10k  DC Current Gain (hFE) (Min) @ Ic, Vce  30 @ 5mA, 10V  Vce Saturation (Max) @ Ib, Ic  250mV @ 300μA, 10mA  Current - Collector Cutoff (Max)  Frequency - Transition  80MHz  Power - Max  300mW  Mounting Type  Through Hole  Package / Case  NS-B1  Supplier Device Package	Transistor Type	PNP - Pre-Biased
Resistor - Base (R1) (Ohms)2.2kResistor - Emitter Base (R2) (Ohms)10kDC Current Gain (hFE) (Min) @ Ic, Vce30 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 300μA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition80MHzPower - Max300mWMounting TypeThrough HolePackage / CaseNS-B1Supplier Device PackageNS-B1	Current - Collector (Ic) (Max)	100mA
Resistor - Emitter Base (R2) (Ohms)10kDC Current Gain (hFE) (Min) @ Ic, Vce30 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 300μA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition80MHzPower - Max300mWMounting TypeThrough HolePackage / CaseNS-B1Supplier Device PackageNS-B1	Voltage - Collector Emitter Breakdown (Max)	50V
DC Current Gain (hFE) (Min) @ Ic, Vce  30 @ 5mA, 10V  Vce Saturation (Max) @ Ib, Ic  250mV @ 300μA, 10mA  Current - Collector Cutoff (Max)  500nA  Frequency - Transition  80MHz  Power - Max  300mW  Mounting Type  Through Hole  Package / Case  NS-B1  Supplier Device Package	Resistor - Base (R1) (Ohms)	2.2k
Vce Saturation (Max) @ Ib, Ic250mV @ 300μA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition80MHzPower - Max300mWMounting TypeThrough HolePackage / CaseNS-B1Supplier Device PackageNS-B1	Resistor - Emitter Base (R2) (Ohms)	10k
Current - Collector Cutoff (Max)  Frequency - Transition  80MHz  Power - Max  300mW  Mounting Type  Through Hole  Package / Case  NS-B1  Supplier Device Package  NS-B1	DC Current Gain (hFE) (Min) @ Ic, Vce	30 @ 5mA, 10V
Frequency - Transition 80MHz  Power - Max 300mW  Mounting Type Through Hole  Package / Case NS-B1  Supplier Device Package NS-B1	Vce Saturation (Max) @ Ib, Ic	250mV @ 300μA, 10mA
Power - Max 300mW  Mounting Type Through Hole Package / Case NS-B1  Supplier Device Package NS-B1	Current - Collector Cutoff (Max)	500nA
Mounting Type Through Hole Package / Case NS-B1 Supplier Device Package NS-B1	Frequency - Transition	80MHz
Package / Case NS-B1 Supplier Device Package NS-B1	Power - Max	300mW
Supplier Device Package NS-B1	Mounting Type	Through Hole
	Package / Case	NS-B1
D ( 0	Supplier Device Package	NS-B1
Report errors?		Report errors?

#### **UNR411H00A Guarantees**



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## **UNR411H00A Payment Methods**





















## **UNR411H00A Shipping Methods**













If you have any question about UNR411H00A, please do not hesitate to contact us!

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